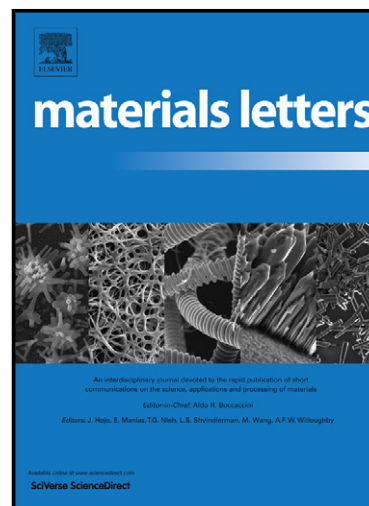


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Thermal conductivity of partially amorphous porous silicon by photoacoustic technique

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Abstract

In this paper, thermal conductivity study of partially amorphous porous silicon obtained by irradiation with swift (110 MeV) uranium ions is reported. Photoacoustic technique allows thermal conductivity evaluation of the samples with enhanced amorphous fraction (>80%). In particular, 3-fold thermal conductivity decrease is shown to be achieved

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